

MICRO ELECTRONICS

2N5249

NPN
SILICON
TRANSISTOR

DESCRIPTION

2N5249 is NPN silicon planar transistor designed for AF small signal amplifier stages.

TO-92B



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCEO	50V
Collector-Base Voltage	VCBO	70V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	100mA
Continuous Power Dissipation	Pd	330mW
Operating & Storage Junction Temperature	Tj, Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LVCEO	50		V	IC = 1mA IB = 0
Collector-Base Breakdown Voltage	BVCBO	70		V	IC = 10µA IE = 0
Emtter-Base Breakdown Voltage	BVEBO	5		V	IE = 10µA IC = 0
Collector Cutoff Current	ICBO		30	nA	VCB = 50V IE = 0
Collector Cutoff Current	ICES		30	nA	VCE = 50V VEB = 0
Emitter Cutoff Current	IEBO		50	nA	VEB = 5V IC = 0
D.C. Current Gain	HFE	40	800		IC = 2mA VCE = 5V
		150			IC = 0.1mA VCE = 5V
Collector-Emitter Saturation Voltage	VCE(sat)		0.125	V	IC = 10mA IB = 1mA
			0.78	V	IC = 10mA IB = 1mA
Base-Emitter Voltage	VBE		0.9	V	IC = 2mA VCE = 10V
Output Capacitance	Cob		4	pF	VCB = 10V f = 1MHz
Noise Figure	NF		3	dB	IC = 0.1mA VCE = 5V
					REB = 5Kohm

Pulse test : pulse width < 300µS, duty cycle < 2%.

